

NPN Silicon Power Transistors High Voltage Planar

MJW18020

The MJW18020 planar High Voltage Power Transistor is specifically Designed for motor control applications, high power supplies and UPS's for which the high reproducibility of DC and Switching parameters minimizes the dead time in bridge configurations.

Features

- High and Excellent Gain Linearity
- Fast and Very Tight Switching Times Parameters t_{si} and t_{fi}
- Very Stable Leakage Current due to the Planar Structure
- High Reliability
- Pb-Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Sustaining Voltage	V_{CEO}	450	Vdc
Collector-Emitter Breakdown Voltage	V_{CES}	1000	Vdc
Collector-Base Voltage	V_{CBO}	1000	Vdc
Emitter-Base Voltage	V_{EBO}	9.0	Vdc
Collector Current – Continuous – Peak (Note 1)	I_C	30 45	Adc
Base Current – Continuous – Peak (Note 1)	I_B	6.0 10	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate Above 25°C	P_D	250 2.0	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

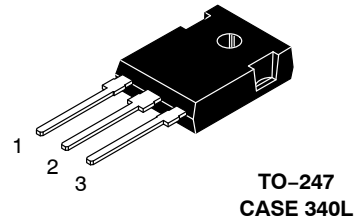
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.5	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T_L	275	$^\circ\text{C}$

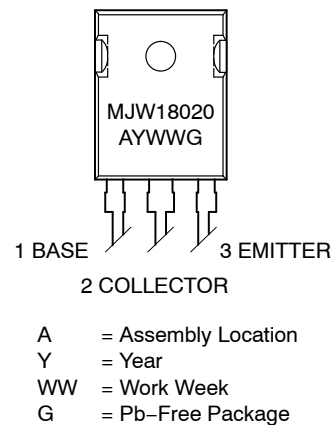
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5 μs , Duty Cycle $\leq 10\%$.

30 AMPERES
1000 VOLTS BV_{CES}
450 VOLTS BV_{CEO} , 250 WATTS



MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping
MJW18020	TO-247	30 Units/Rail
MJW18020G	TO-247 (Pb-Free)	30 Units/Rail

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage ($I_C = 100\text{ mAdc}$, $I_B = 0$)	$V_{CE(sus)}$	450	–	–	Vdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEO}$, $I_B = 0$)	I_{CEO}	–	–	100	μAdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CES}$, $V_{EB} = 0$) ($T_C = 125^\circ\text{C}$)	I_{CES}	–	–	100 500	μAdc
Emitter Cutoff Current ($V_{CE} = 9\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	–	100	μAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 3\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($T_C = 125^\circ\text{C}$)	h_{FE}	14	–	34	
($I_C = 10\text{ Adc}$, $V_{CE} = 2\text{ Vdc}$) ($T_C = 125^\circ\text{C}$)		–	30	–	
($I_C = 20\text{ Adc}$, $V_{CE} = 2\text{ Vdc}$) ($T_C = 125^\circ\text{C}$)		8	16	–	
($I_C = 10\text{ mAdc}$, $V_{CE} = 5\text{ Vdc}$) ($T_C = 125^\circ\text{C}$)		5	14	–	
		5.5	9	–	
		4	7	–	
		14	25	–	
Base-Emitter Saturation Voltage ($I_C = 10\text{ Adc}$, $I_B = 2\text{ Adc}$) ($I_C = 20\text{ Adc}$, $I_B = 4\text{ Adc}$)	$V_{BE(sat)}$	–	0.97 1.15	1.25 1.5	Vdc
Collector-Emitter Saturation Voltage ($I_C = 10\text{ Adc}$, $I_B = 2\text{ Adc}$) ($T_C = 125^\circ\text{C}$)	$V_{CE(sat)}$	–	0.2	0.6	Vdc
($I_C = 20\text{ Adc}$, $I_B = 4\text{ Adc}$) ($T_C = 125^\circ\text{C}$)		–	0.3	–	
		–	0.5	1.5	
		–	0.9	2.0	

DYNAMIC CHARACTERISTICS

Current Gain Bandwidth Product ($I_C = 1\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 1\text{ MHz}$)	f_T	–	13	–	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f_{test} = 1\text{ MHz}$)	C_{ob}	–	300	500	pF
Input Capacitance ($V_{EB} = 8.0$)	C_{ib}	–	7000	9000	pF

SWITCHING CHARACTERISTICS: Resistive Load (D.C. = 10%, Pulse Width = 70 μs)

Turn-On Time	(I _C = 10 Adc, I _{B1} = I _{B2} = 2 Adc, V _{CC} = 125 V)	t _{On}	–	540	750	ns
Storage Time		t _s	–	4.75	6	μs
Fall Time		t _f	–	380	500	ns
Turn-Off Time		t _{Off}	–	5.2	6.5	μs
Turn-On Time	(I _C = 20 Adc, I _{B1} = I _{B2} = 4 Adc, V _{CC} = 125 V)	t _{On}	–	965	1200	ns
Storage Time		t _s	–	2.9	3.5	μs
Fall Time		t _f	–	350	500	ns
Turn-Off Time		t _{Off}	–	3.25	4	μs

SWITCHING CHARACTERISTICS: Inductive Load ($V_{clamp} = 300\text{ V}$, $V_{CC} = 15\text{ V}$, $L = 200\text{ }\mu\text{H}$)

Fall Time	(I _C = 10 Adc, I _{B1} = I _{B2} = 2 Adc)	t _{fi}	–	142	250	ns
Storage Time		t _{si}	–	4.75	6	μs
Crossover Time		t _c	–	320	500	ns
Fall Time	(I _C = 20 Adc, I _{B1} = I _{B2} = 4 Adc)	t _{fi}	–	350	500	ns
Storage Time		t _{si}	–	3.0	3.5	μs
Crossover Time		t _c	–	500	750	ns

TYPICAL CHARACTERISTICS

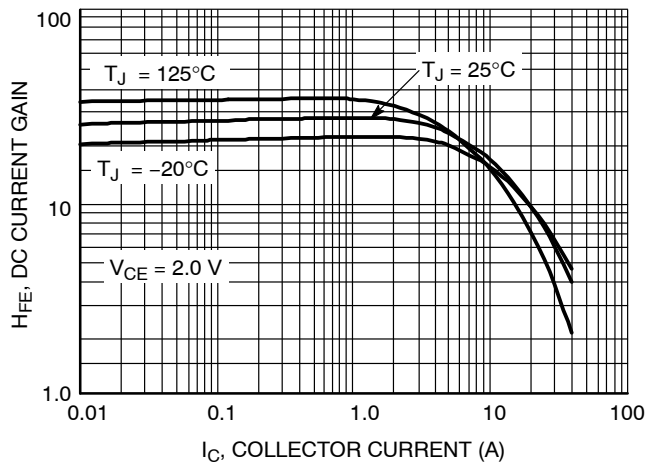


Figure 1. DC Current Gain, $V_{CE} = 2.0$ V

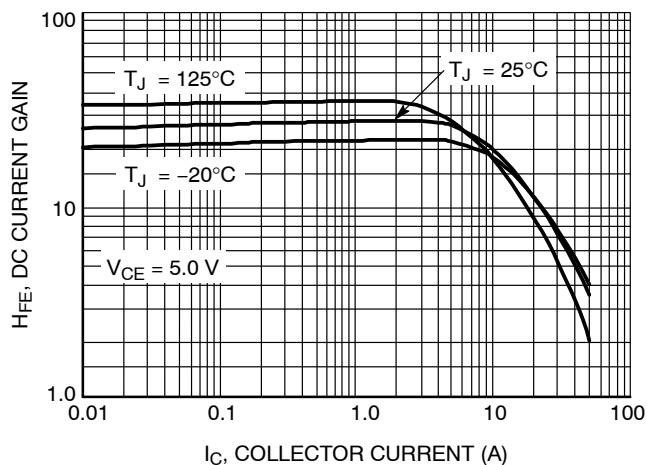


Figure 2. DC Current Gain, $V_{CE} = 5.0$ V

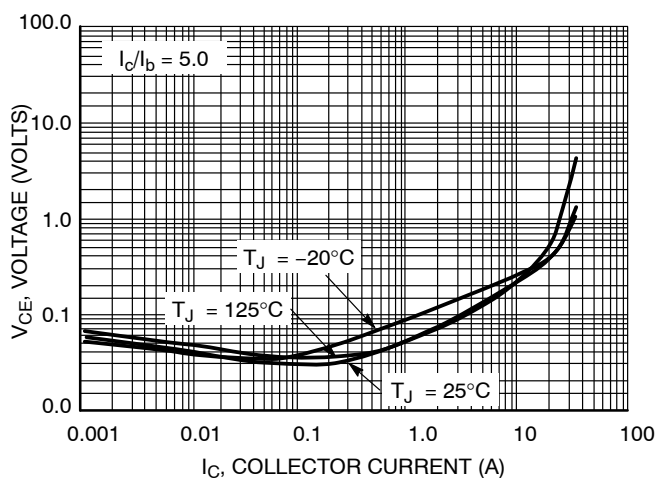


Figure 3. Typical Collector-Emitter Saturation Voltage, $I_C/I_B = 5.0$

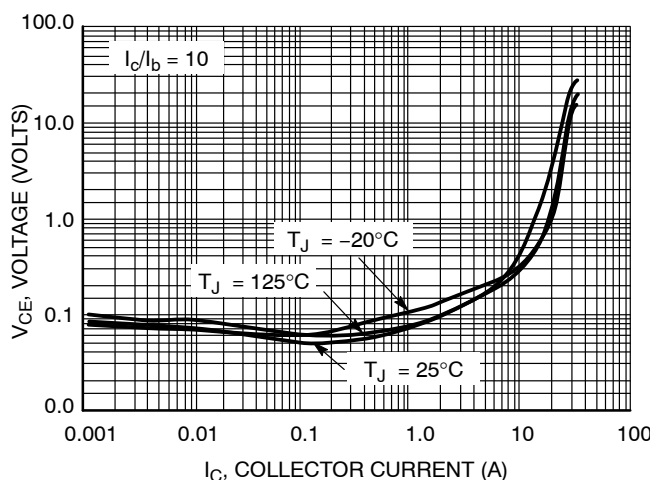


Figure 4. Typical Collector-Emitter Saturation Voltage, $I_C/I_B = 10$

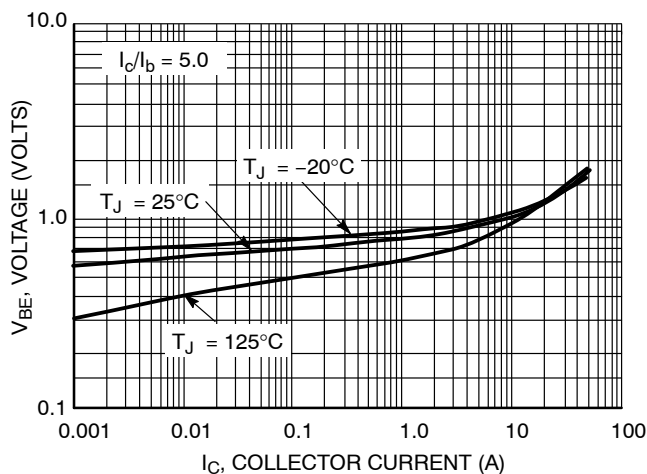


Figure 5. Typical Base-Emitter Saturation Voltage, $I_C/I_B = 5.0$

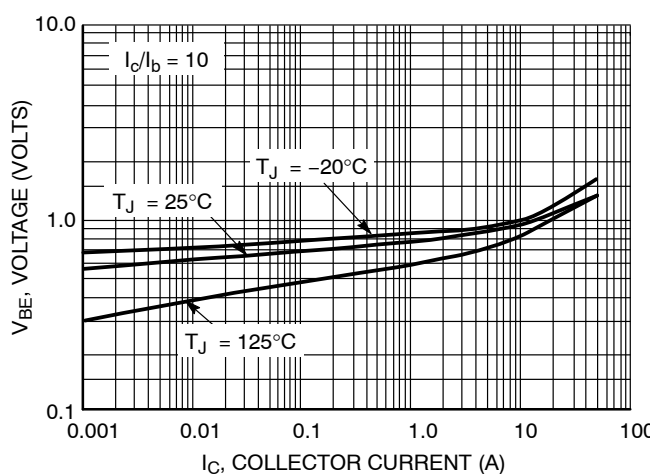


Figure 6. Typical Base-Emitter Saturation Voltage, $I_C/I_B = 10$

TYPICAL CHARACTERISTICS

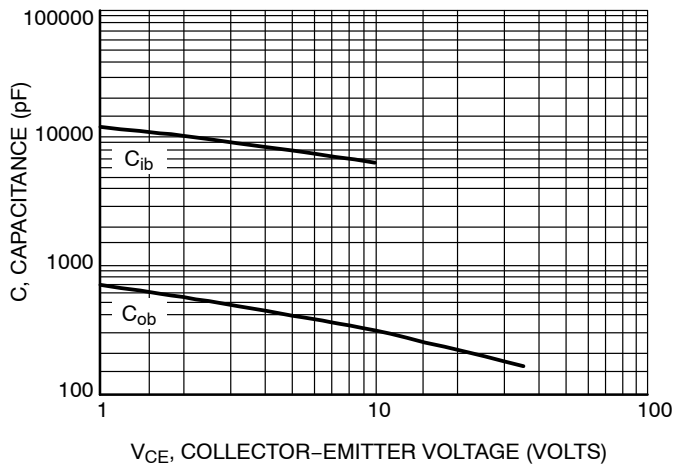


Figure 7. Typical Capacitance

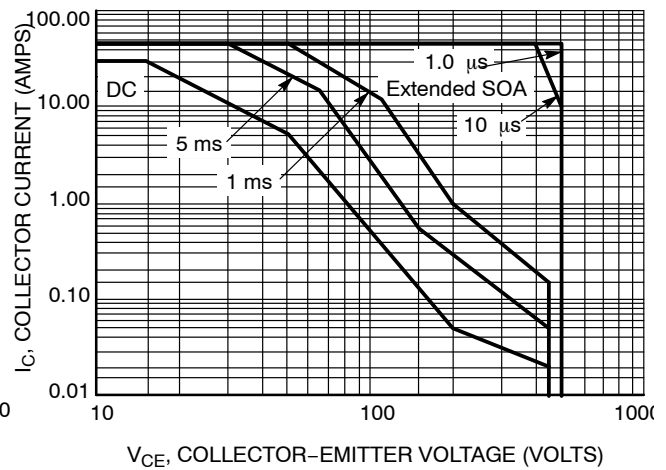


Figure 8. Forward Bias Safe Operating Area

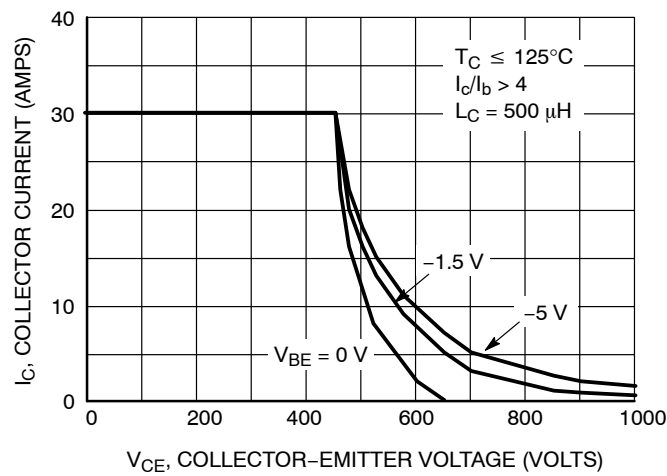
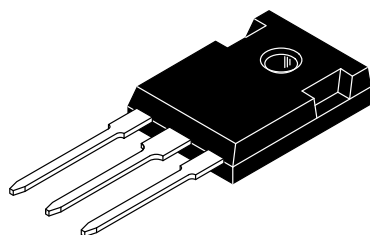


Figure 9. Reverse Bias Safe Operating Area



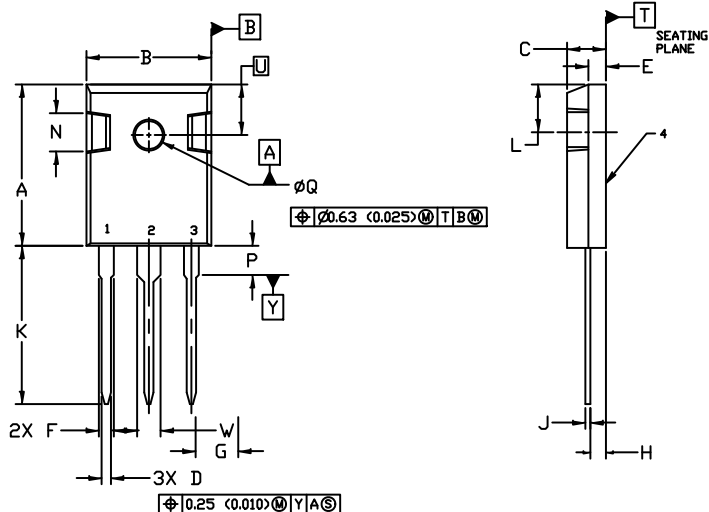
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CASE 340L
ISSUE G

DATE 06 OCT 2021

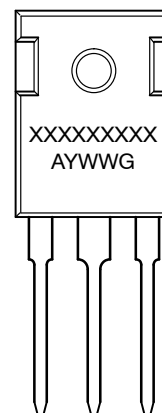
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER



	MILLIMETERS		INCHES	
DIM	MIN.	MAX.	MIN.	MAX.
A	20.32	21.08	0.800	0.830
B	15.75	16.26	0.620	0.640
C	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
E	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45	BSC	0.215	BSC
H	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P	----	4.50	----	0.177
Q	3.55	3.65	0.140	0.144
U	6.15	BSC	0.242	BSC
W	2.87	3.12	0.113	0.123

GENERIC MARKING DIAGRAM*



- | | | | |
|----------------|------------------------|--------------|--------------|
| STYLE 1: | STYLE 2: | STYLE 3: | STYLE 4: |
| PIN 1. GATE | PIN 1. ANODE | PIN 1. BASE | PIN 1. GATE |
| 2. DRAIN | 2. CATHODE (S) | 2. COLLECTOR | 2. COLLECTOR |
| 3. SOURCE | 3. ANODE 2 | 3. EMITTER | 3. EMITTER |
| 4. DRAIN | 4. CATHODES (S) | 4. COLLECTOR | 4. COLLECTOR |
| | | | |
| STYLE 5: | STYLE 6: | | |
| PIN 1. CATHODE | PIN 1. MAIN TERMINAL 1 | | |
| 2. ANODE | 2. MAIN TERMINAL 2 | | |
| 3. GATE | 3. GATE | | |
| 4. ANODE | 4. MAIN TERMINAL 2 | | |

XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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